

Product Summary

Part #	V_{DS}	$R_{DS(on)}$	I_D ($T_{vj}=25^{\circ}C$)
DPM065R040K3G1	650V	28m Ω	74A

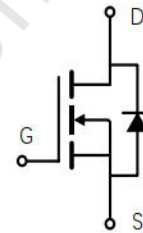
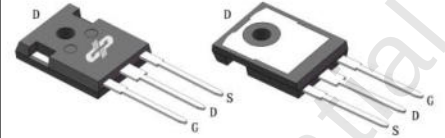
Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(on)}$
- Easy to parallel
- RoHS Compliant

Applications

- General purpose drives
- Energy storage systems
- String inverter
- Uninterruptible power supplies

TO247-3L



Package Marking and Ordering Information

Part #	Marking	Package	Packing
DPM065R040K3G1	M065R040	TO247-3L	Tube



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Continuous drain current ($V_{GS}=18V$)	I_D	74	A
$T_C = 25^{\circ}C$		52	
$T_C = 100^{\circ}C$			
Pulsed drain current ($T_C = 25^{\circ}C$, t_p limited by T_{jmax})	$I_{D\ pulse}$	222	A
Gate-source voltage, max. transient voltage	V_{GSmax}	-8/+22	V
Gate-source voltage, max. static voltage	V_{GSop}	-4/+18	V
Power dissipation ($T_C = 25^{\circ}C$)	P_{tot}	250	W
Power dissipation ($T_C = 100^{\circ}C$)		125	
Operating junction temperature	T_j	-40...+175	$^{\circ}C$
Storage temperature	T_{stg}	-40...+150	$^{\circ}C$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – mounting base	R_{thMB}	0.6	°C/W

Electrical Characteristic (at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2	2.6 1.9	4	V	$V_{DS}=V_{GS}, I_D=10mA$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$
Zero gate voltage drain current	I_{DSS}	-	1	10	μA	$V_{DS}=650V, V_{GS}=0V$ $T_j=25^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	250	nA	$V_{GS}=18V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	28 34	36	m Ω	$V_{GS}=18V, I_D=30A$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$
Gate resistance	R_g	-	4	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Dynamic Characteristic^[2]

Input Capacitance	C_{iss}	-	2235	-	pF	$V_{GS}=0V, V_{DS}=600V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	199	-		
Reverse Transfer Capacitance	C_{rss}	-	12	-		
Gate Total Charge	Q_g	-	105	-	nC	$V_{GS}=-4/18V, V_{DS}=400V,$ $I_D=30A, f=1MHz$
Gate-Source charge	Q_{gs}	-	28	-		
Gate-Drain charge	Q_{gd}	-	32	-		
Turn-on delay time	$t_{d(on)}$	-	14	-	ns	$V_{GS}=-4/18V, I_D=30A,$ $V_{DD}=400V, R_{G_ext}=2.5\Omega$ $L=200\mu H$
Rise time	t_r	-	17	-		
Turn-off delay time	$t_{d(off)}$	-	28	-		
Fall time	t_f	-	7	-		
Turn-On Energy	E_{on}	-	87	-	μJ	
Turn-Off Energy	E_{off}	-	25	-		

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	4.2 3.6	6.3	V	$V_{GS} = -4V, I_{SD} = 30A$ $T_j = 25^\circ C$ $T_j = 175^\circ C$
Diode continuous forward current	I_s		37 20	- -	A	$V_{GS} = -4V$ $T_C = 25^\circ C$ $T_C = 100^\circ C$
Diode Peak reverse recovery Current	I_{rrm}	-	9	-	A	$V_{GS} = -4V, V_R = 400V$ $I_{SD} = 30A, dI/dt = 1797A/\mu s$
Body Diode Reverse Recovery Time ^[2]	t_{rr}	-	18	-	ns	
Body Diode Reverse Recovery Charge ^[2]	Q_{rr}	-	235	-	nC	

[2]. Defined by design. Not subject to production test

Typical Performance Characteristics

Fig 1: Output Characteristics

$T_j = -40^\circ\text{C}$

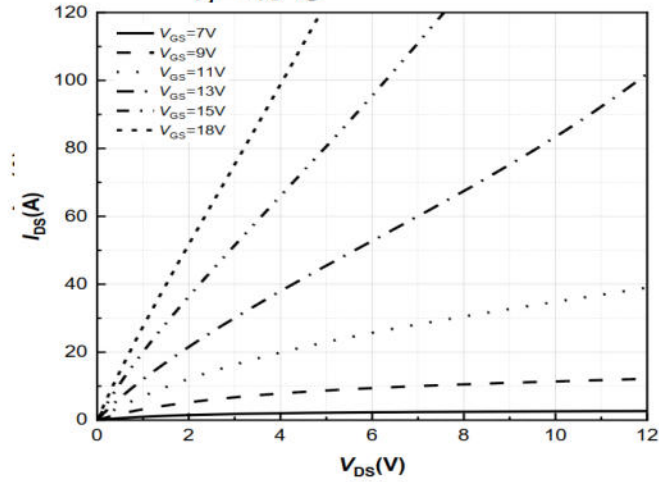


Fig 2: Output Characteristics

$T_j = 25^\circ\text{C}$

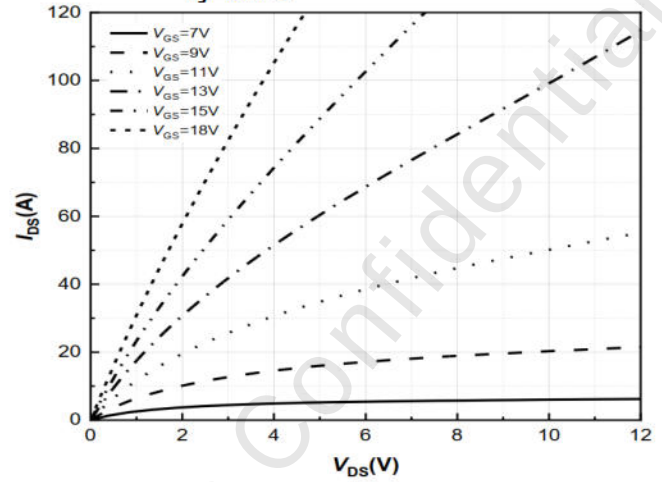


Fig 3: Output Characteristics

$T_j = 175^\circ\text{C}$

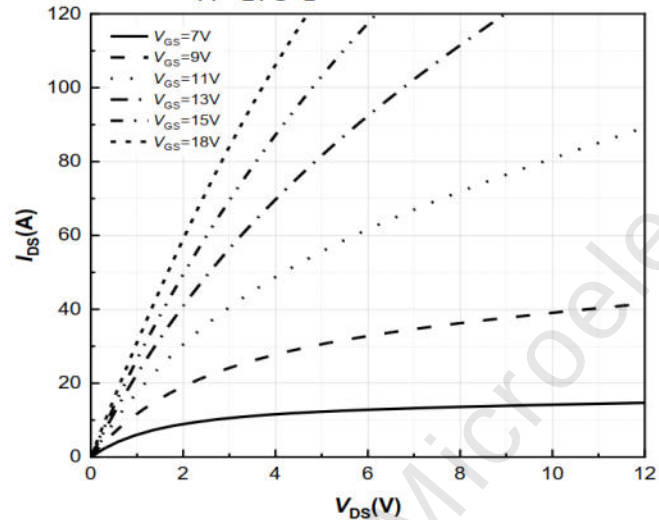


Fig 4: $R_{ds(on)}$ vs Temperature

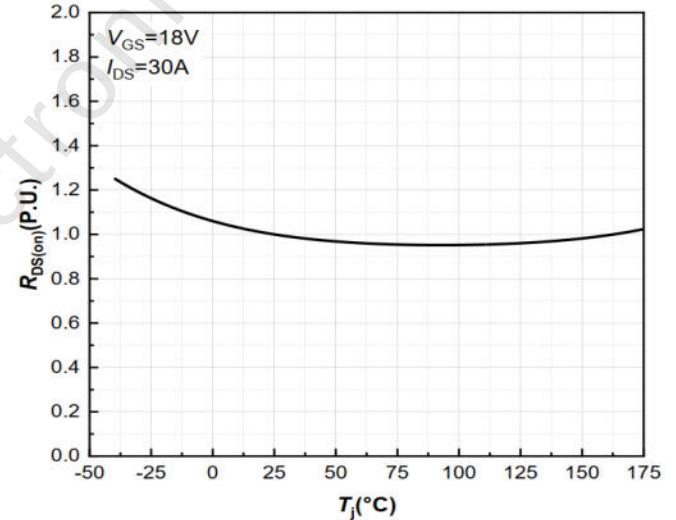


Fig 5: $R_{ds(on)}$ vs Drain Current for various Temperature

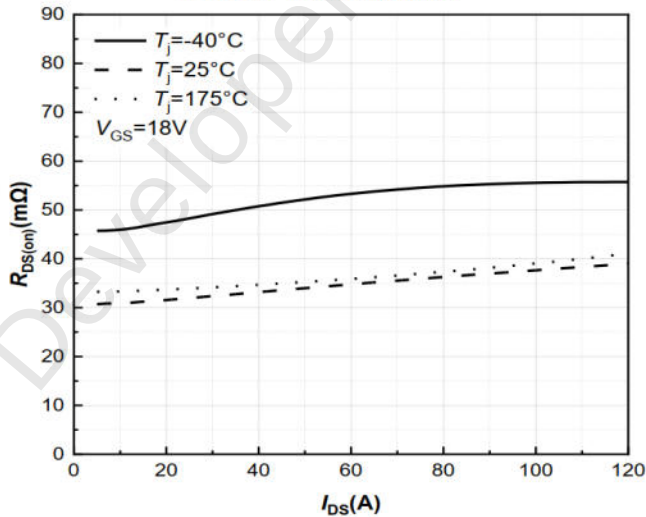
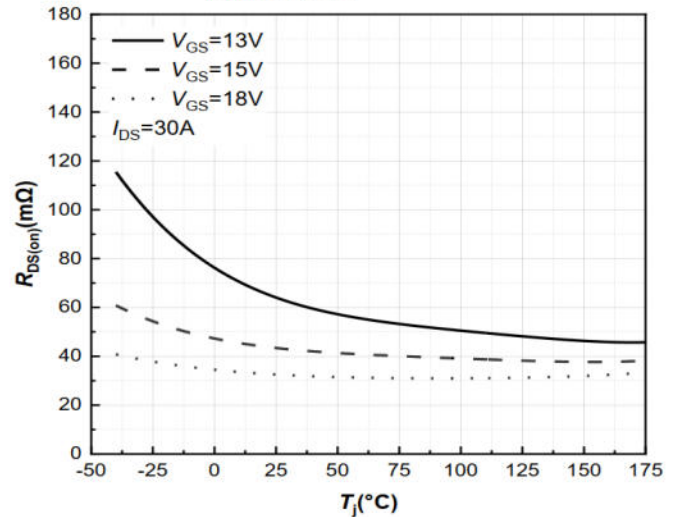


Fig 7: $R_{ds(on)}$ vs. Gate Voltage at Temperature



Typical Performance Characteristics

Fig 7: Transfer Characteristics

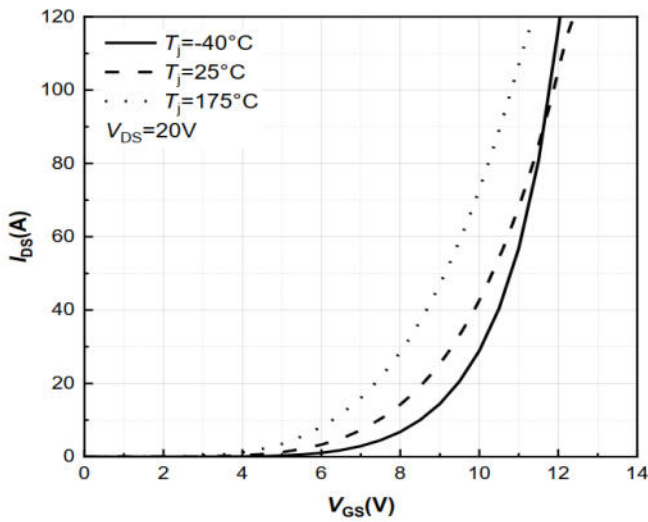


Fig 8: Body Diode Characteristic $T_j = -40^\circ\text{C}$

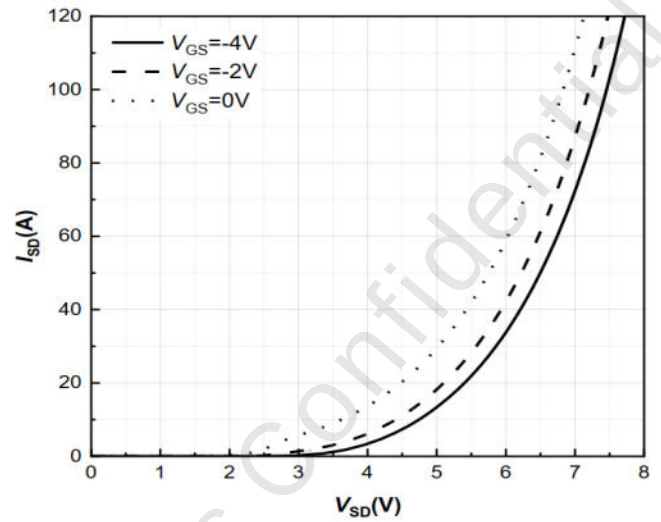


Fig 9: Body Diode Characteristic
 $T_j = 25^\circ\text{C}$

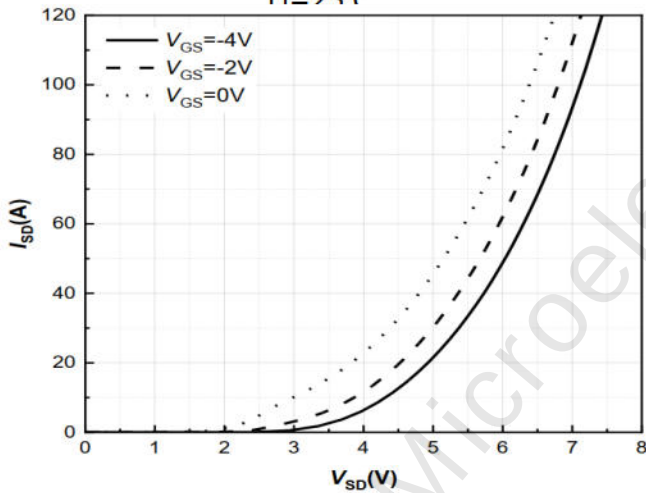


Fig 10: Body Diode Characteristic
 $T_j = 175^\circ\text{C}$

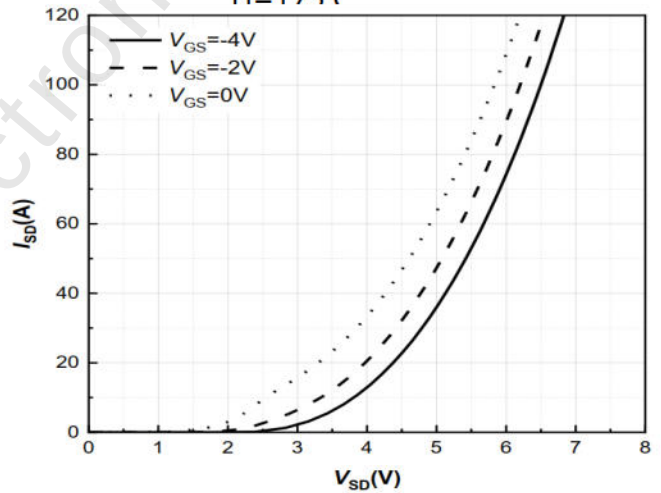


Fig 11: Threshold Voltage vs. Temperature

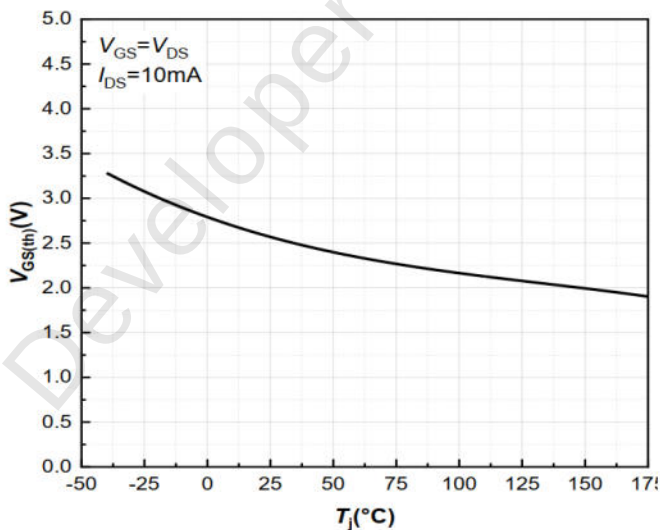


Fig 12: Capacitance Characteristics

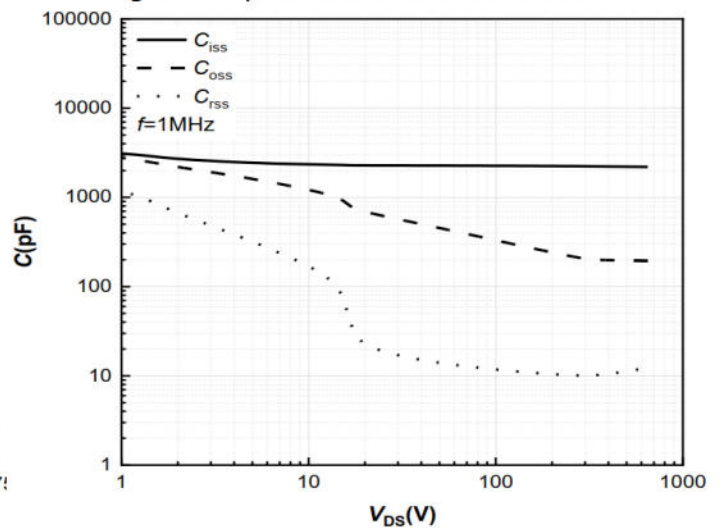


Fig 13: Gate Charge Characteristics

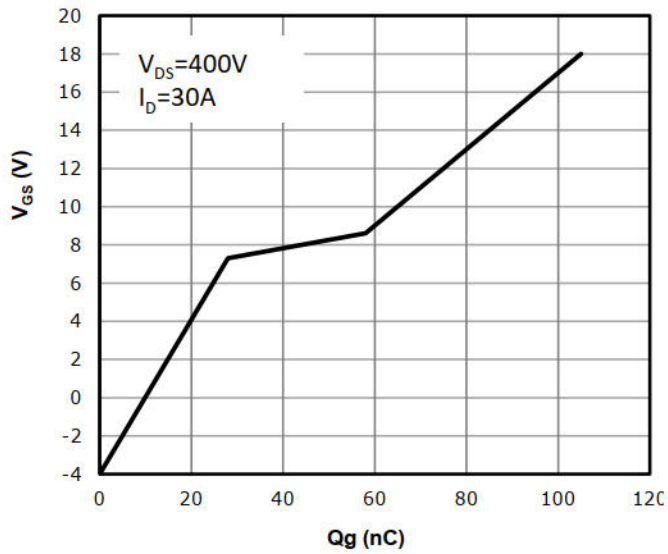


Fig 14: Clamped Inductive Switching energy vs R_g

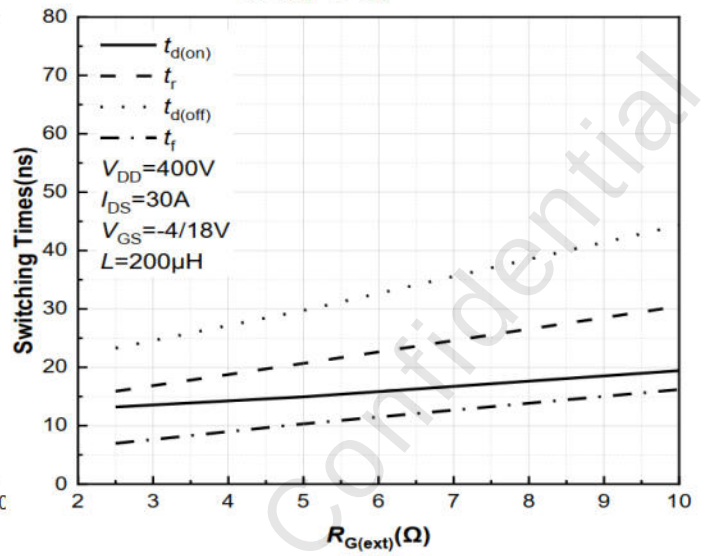


Fig 15: Power Dissipation

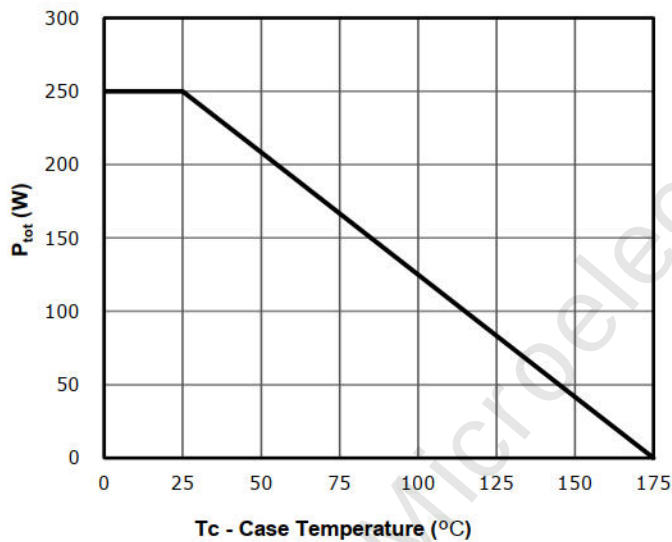


Fig 16: Drain Current Derating

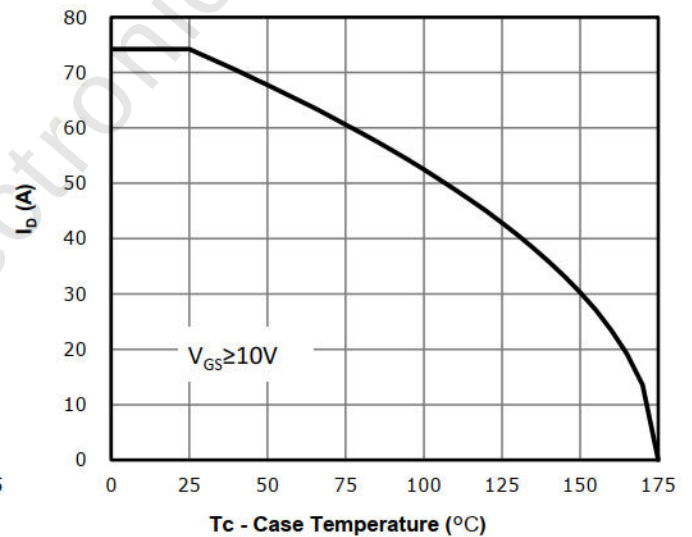


Fig 17: Safe Operating Area

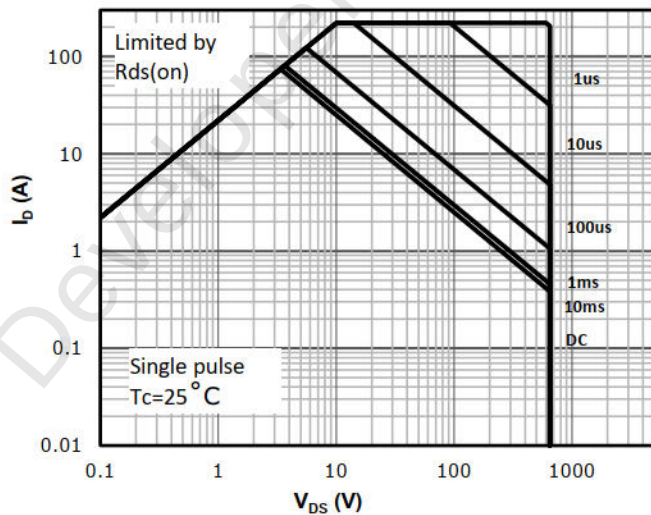
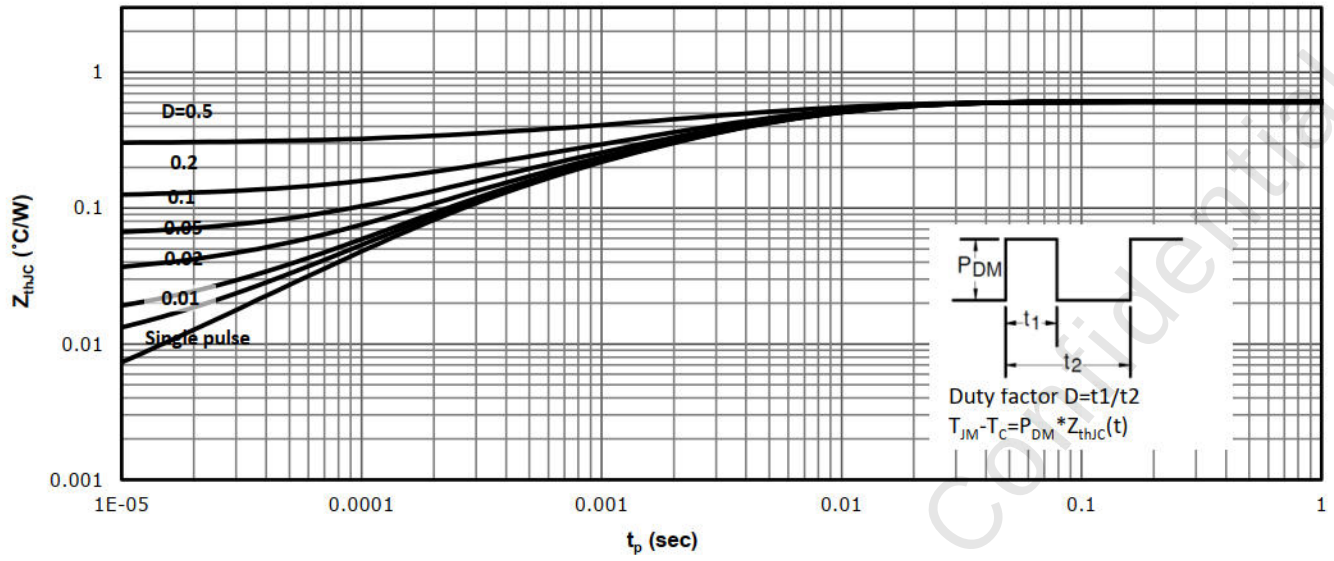
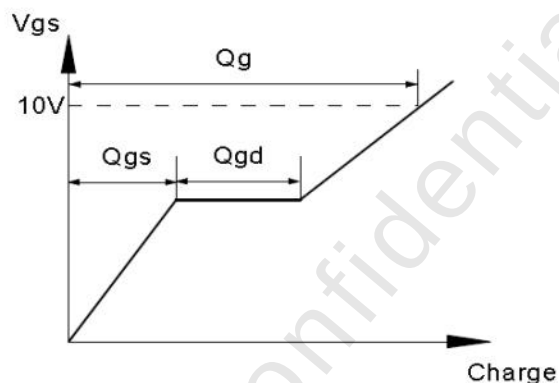
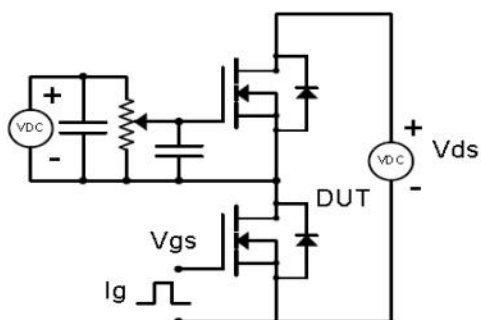


Fig 18: Max. Transient Thermal Impedance

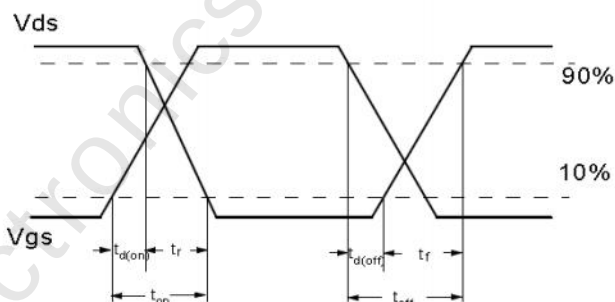
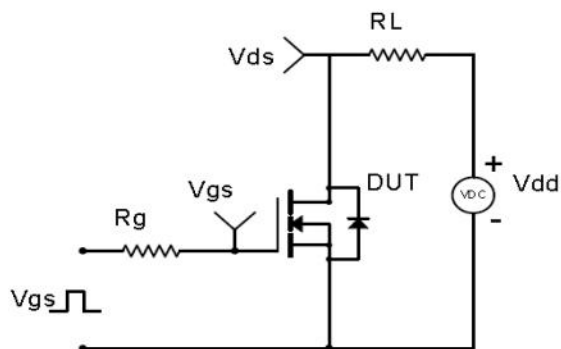


Test Circuit & Waveform

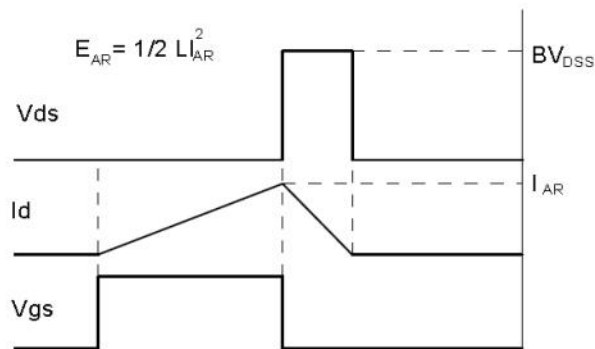
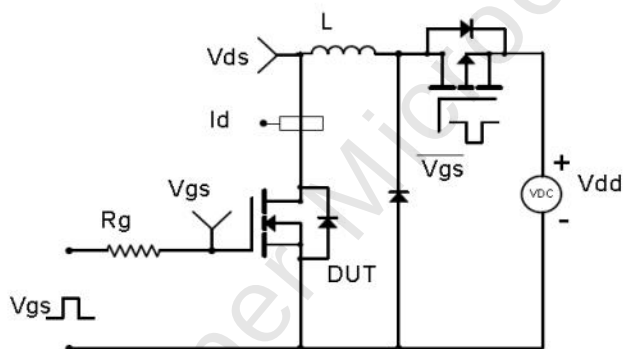
Gate Charge Test Circuit & Waveform



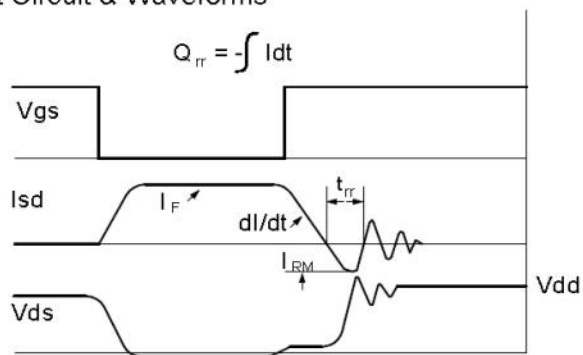
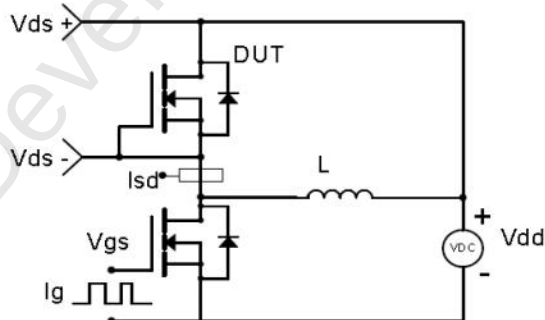
Resistive Switching Test Circuit & Waveforms



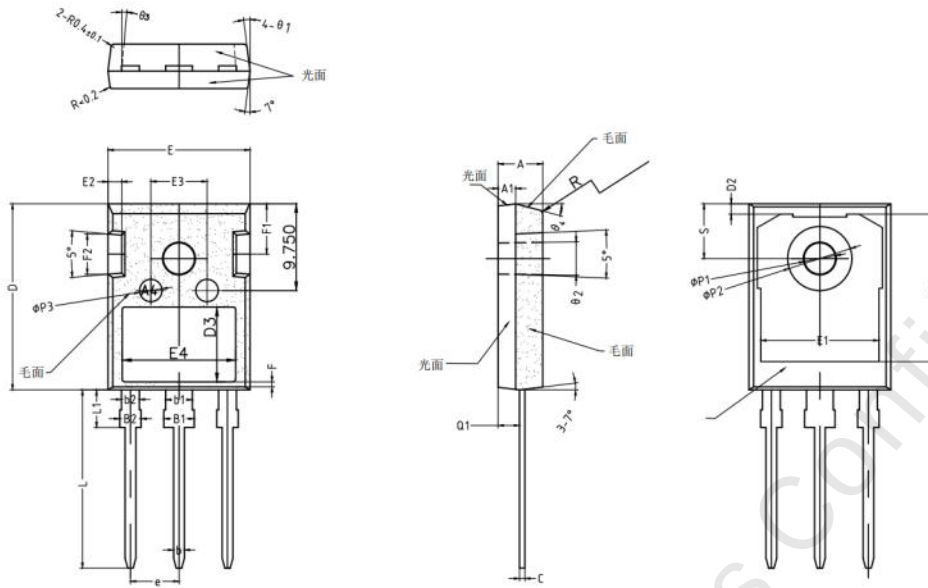
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

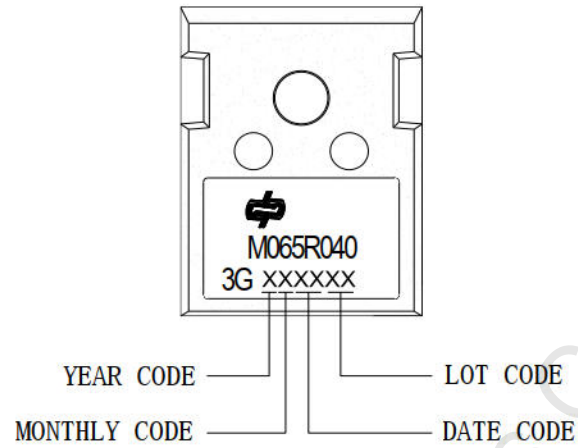


Package Outline: TO247



Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	1.90	2.00	2.10
b	1.15	1.20	1.25
b1	2.95	3.00	3.05
b2	1.95	2.00	2.05
B1	3.00	3.10	3.20
B2	1.90	2.00	2.10
c	0.55	0.60	0.65
D	20.90	21.00	21.10
D1	16.45	16.55	16.65
D2	1.07	1.17	1.27
D3	8.15	8.20	8.25
E	15.70	15.80	15.90
E1	13.16	13.26	13.36
E2	2.40	2.50	2.60
E3	6.10	6.20	6.30
E4	12.70	12.80	12.90
F	0.75	0.85	0.95
F1	5.70	5.80	5.90
F2	4.90	5.00	5.10
F3	9.90	10.00	10.10
e	5.44 BSC		
L	19.72	19.92	20.12
L1	4.03	4.13	4.23
theta1	5°	7°	9°
theta2	1°	2°	3°
theta3	4°	5°	6°
theta4	13°	15°	17°
phi P1	3.50	3.60	3.70
phi P2	7.09	7.19	7.29
phi P3	2.40	2.50	2.60
Q1	2.31	2.41	2.51
S	6.05	6.15	6.25
R	0.30	0.40	0.50

Part Marking Information



Revision History

Revision	Major changes
1.0	Release for formal version1.0

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